

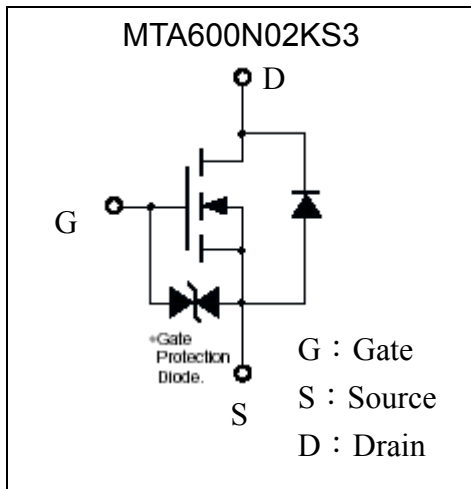
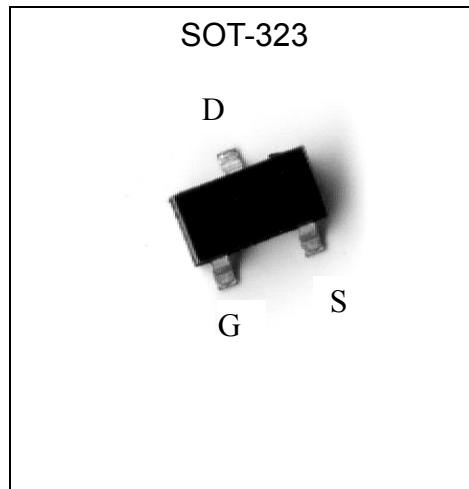
N-Channel MOSFET

MTA600N02KS3

Features

- Low on-resistance
- ESD protected gate
- High speed switching
- Low-voltage drive
- Easily designed drive circuits
- Easy to use in parallel
- Pb-free lead plating and halogen-free package

BV_{DSS}	20V
$I_D @ V_{GS}=4.5V, T_A=25^{\circ}C$	0.55A
$R_{DS(on)} @ V_{GS}=4.5V, I_D=0.5A$	0.213 Ω (typ.)
$R_{DS(on)} @ V_{GS}=2.5V, I_D=0.5A$	0.275 Ω (typ.)
$R_{DS(on)} @ V_{GS}=1.8V, I_D=0.05A$	0.332 Ω (typ.)
$R_{DS(on)} @ V_{GS}=1.5V, I_D=0.02A$	0.447 Ω (typ.)
$R_{DS(on)} @ V_{GS}=1.2V, I_D=0.01A$	0.937 Ω (typ.)

Symbol

Outline

Ordering Information

Device	Package	Shipping
MTA600N02KS3-0-T1-G	SOT-323 (Pb-free lead plating and halogen-free package)	3000 pcs / Tape & Reel

- ↑ Environment friendly grade : S for RoHS compliant products, G for RoHS compliant and green compound products
- ↑ Packing spec, T1 : 3000 pcs / tape & reel, 7" reel
- ↑ Product rank, zero for no rank products
- ↑ Product name

**Absolute Maximum Ratings** (Ta=25°C)

Parameter		Symbol	Limits	Unit
Drain-Source Voltage		V _{DSS}	20	V
Gate-Source Voltage		V _{GSS}	±8	
Drain Current	Continuous @ V _{GS} =4.5V, T _A =25°C	I _D	550	mA
	Pulsed	I _{DP}	2.2 *1	
Total Power Dissipation		P _D	150 *2	mW
Thermal Resistance, Junction to Ambient		R _{θJA}	833 *2	°C/W
Operating Junction Temperature Range		T _j	-55~+150	°C
Storage Temperature Range		T _{stg}	-55~+150	

Note : *1. Pulse Width ≤ 300μs, Duty cycle ≤ 5%

*2. When the device is mounted on a minimum pad size

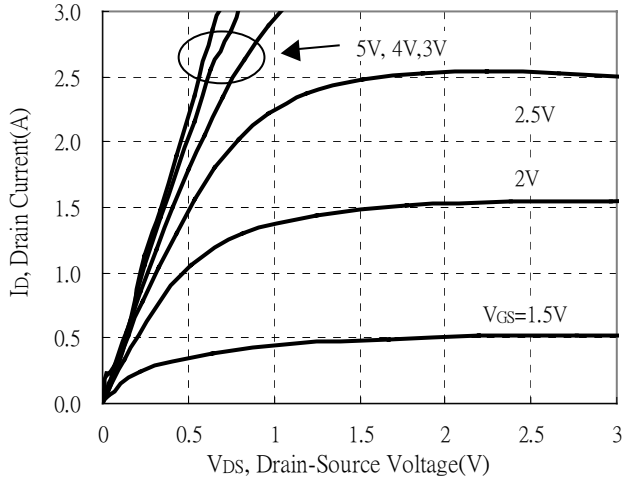
Electrical Characteristics (Ta=25°C)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
BV _{DSS} *	20	-	-	V	V _{GS} =0V, I _D =10μA
V _{GS(th)}	0.4	-	1.0		V _{DS} =V _{GS} , I _D =250μA
I _{GSS}	-	-	±10	μA	V _{GS} =±8V, V _{DS} =0V
I _{DSS}	-	-	1		V _{DS} =20V, V _{GS} =0V
R _{DS(ON)} *	-	0.213	0.55	Ω	V _{GS} =4.5V, I _D =500mA
	-	0.275	0.9		V _{GS} =2.5V, I _D =500mA
	-	0.332	4.2		V _{GS} =1.8V, I _D =50mA
	-	0.447	5.5		V _{GS} =1.5V, I _D =20mA
	-	0.937	6.5		V _{GS} =1.2V, I _D =10mA
G _{FS}	400	847	-	mS	V _{DS} =10V, I _D =300mA
Dynamic					
C _{iss}	-	42	-	pF	V _{DS} =10V, V _{GS} =0V, f=1MHz
C _{oss}	-	19	-		
C _{rss}	-	13	-		
t _{d(ON)}	-	6	-	ns	V _{DS} =10V, I _D =500mA, V _{GS} =4.5V, R _G =6Ω
t _r	-	17.8	-		
t _{d(OFF)}	-	32.2	-		
t _f	-	20.2	-		
Q _g	-	1.2	-	nC	V _{DS} =10V, I _D =1A, V _{GS} =4.5V
Q _{gs}	-	0.43	-		
Q _{gd}	-	0.3	-		
Source-Drain Diode					
*V _{SD}	-	0.85	1.2	V	V _{GS} =0V, I _S =500mA
*t _{rr}	-	4.6	-	ns	I _F =1A, dI _F /dt=100A/μs
*Q _{rr}	-	0.57	-	nC	

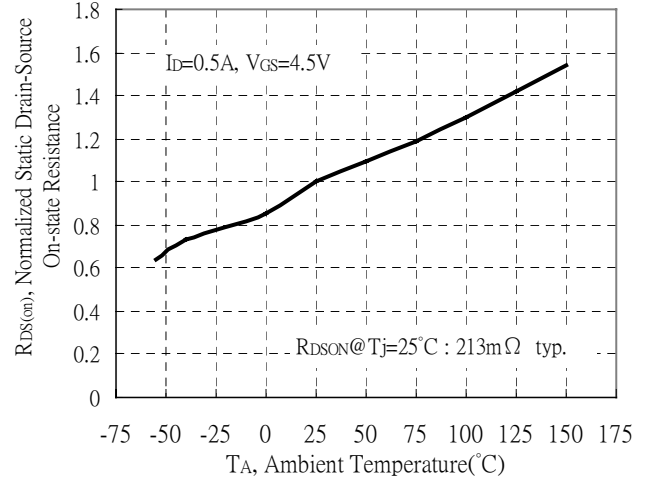
*Pulse Test : Pulse Width ≤ 380μs, Duty Cycle ≤ 2%

Typical Characteristics

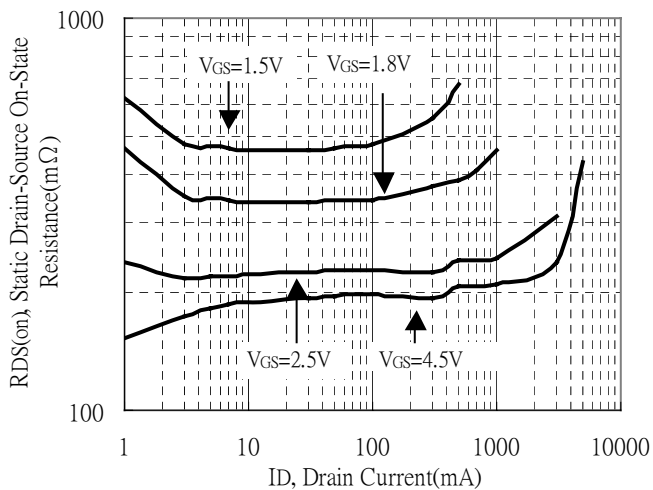
Typical Output Characteristics



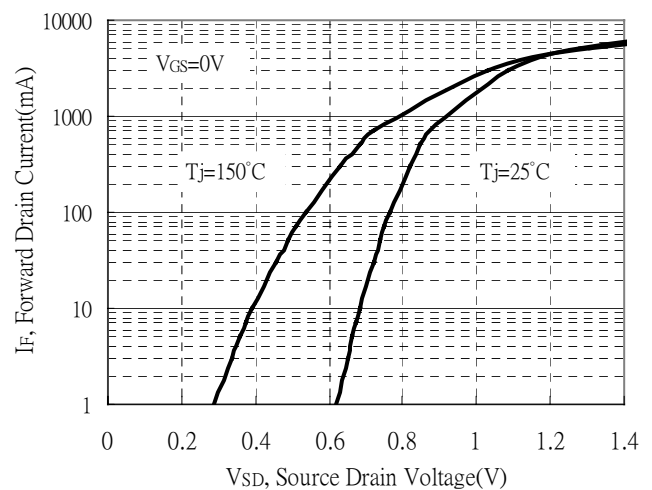
Static Drain-Source On-resistance vs Ambient Temperature



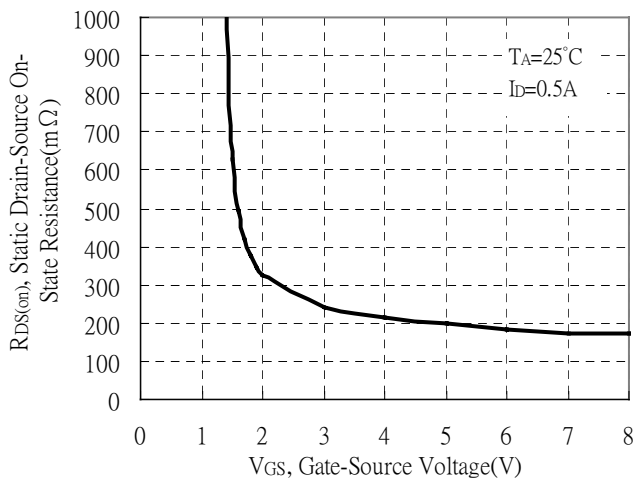
Static Drain-Source On-State resistance vs Drain Current



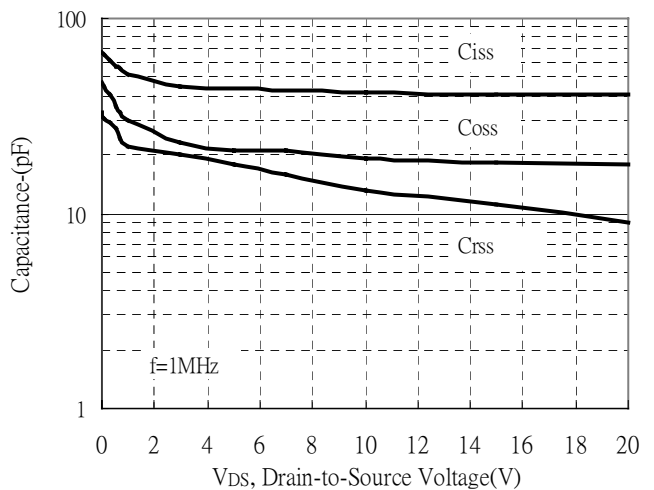
Forward Drain Current vs Source-Drain Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage

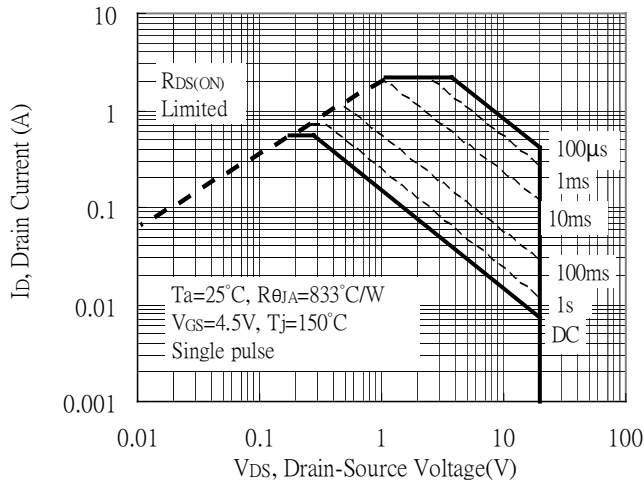


Capacitance vs Reverse Voltage

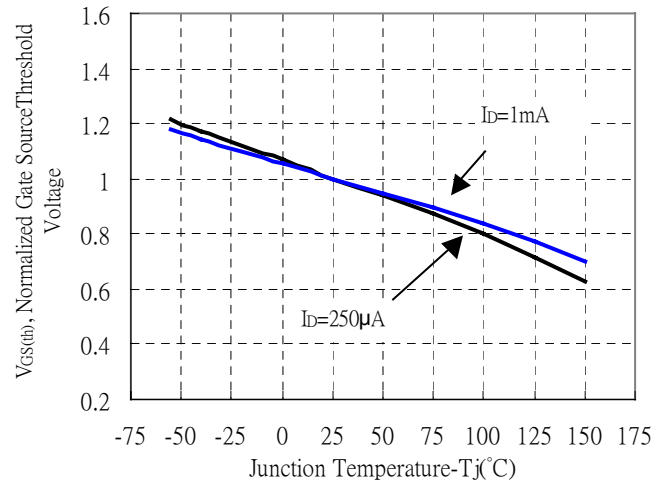


Typical Characteristics(Cont.)

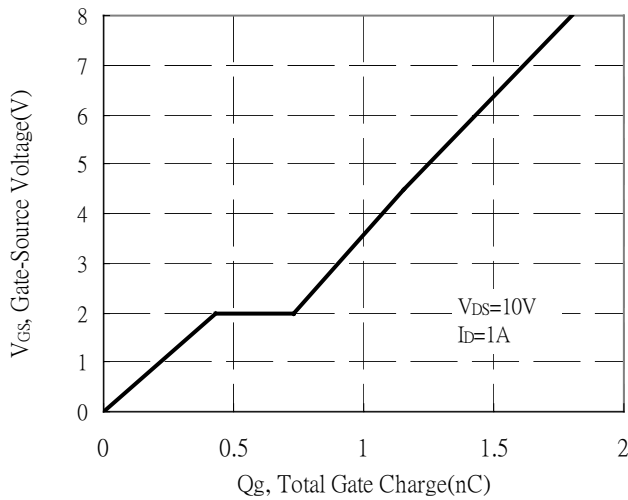
Maximum Safe Operating Area



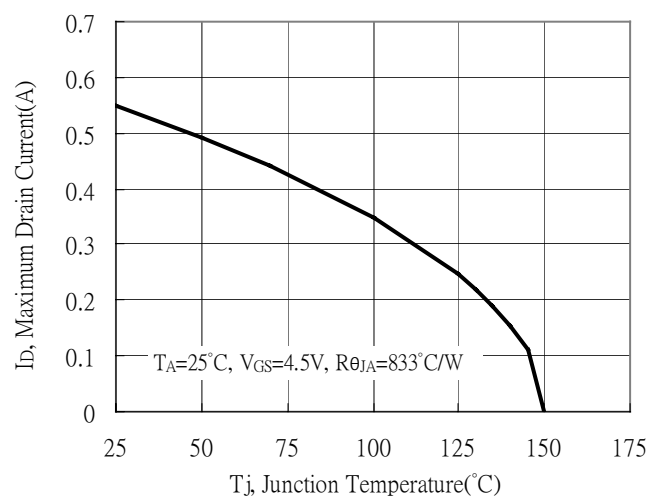
Gate Threshold Voltage vs Ambient Temperature



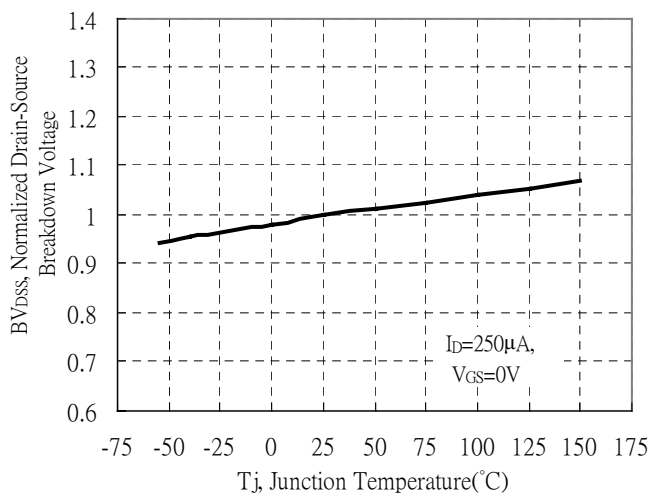
Gate Charge Characteristics



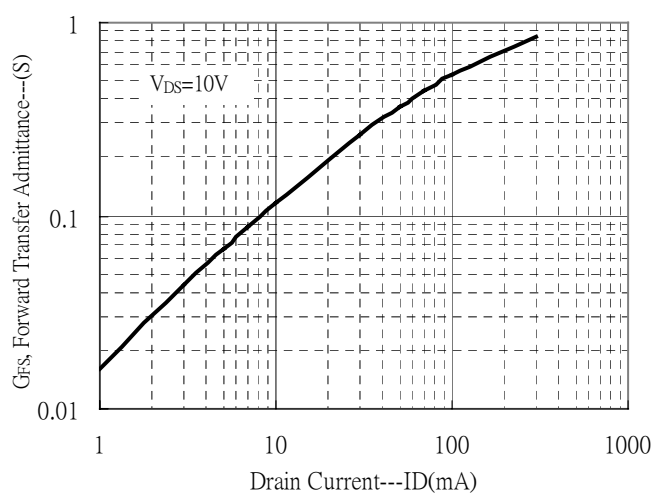
Maximum Drain Current vs Junction Temperature



Breakdown Voltage vs Ambient Temperature

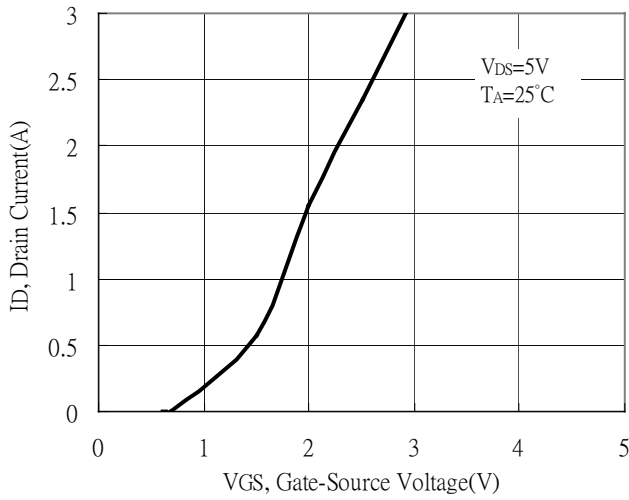


Forward Transfer Admittance vs Drain Current

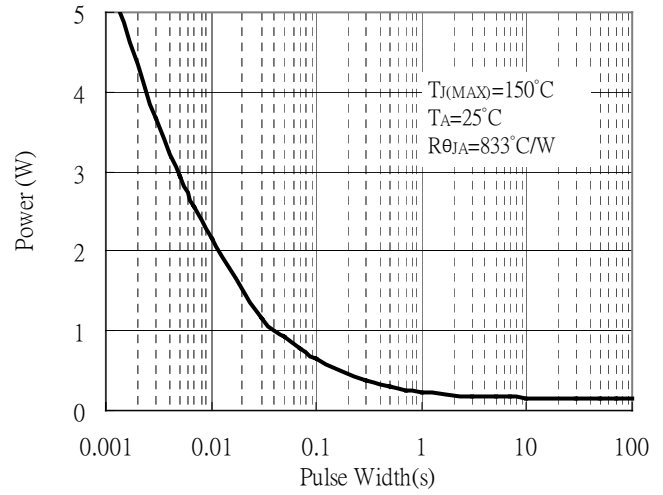


Typical Characteristics(Cont.)

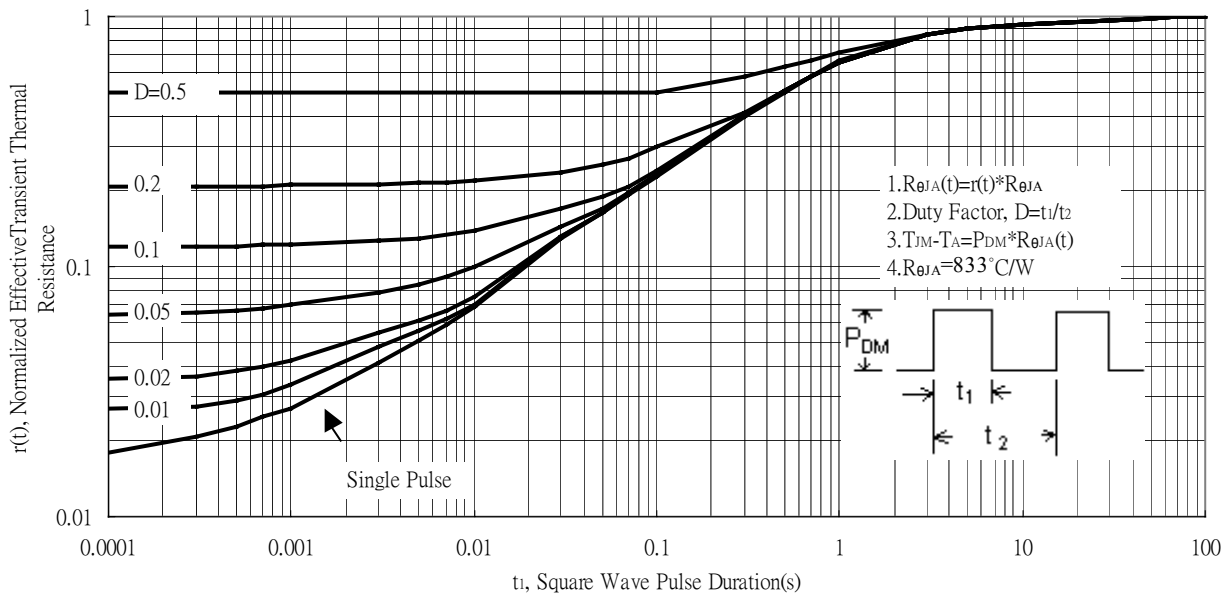
Drain Current vs Gate-Source Voltage



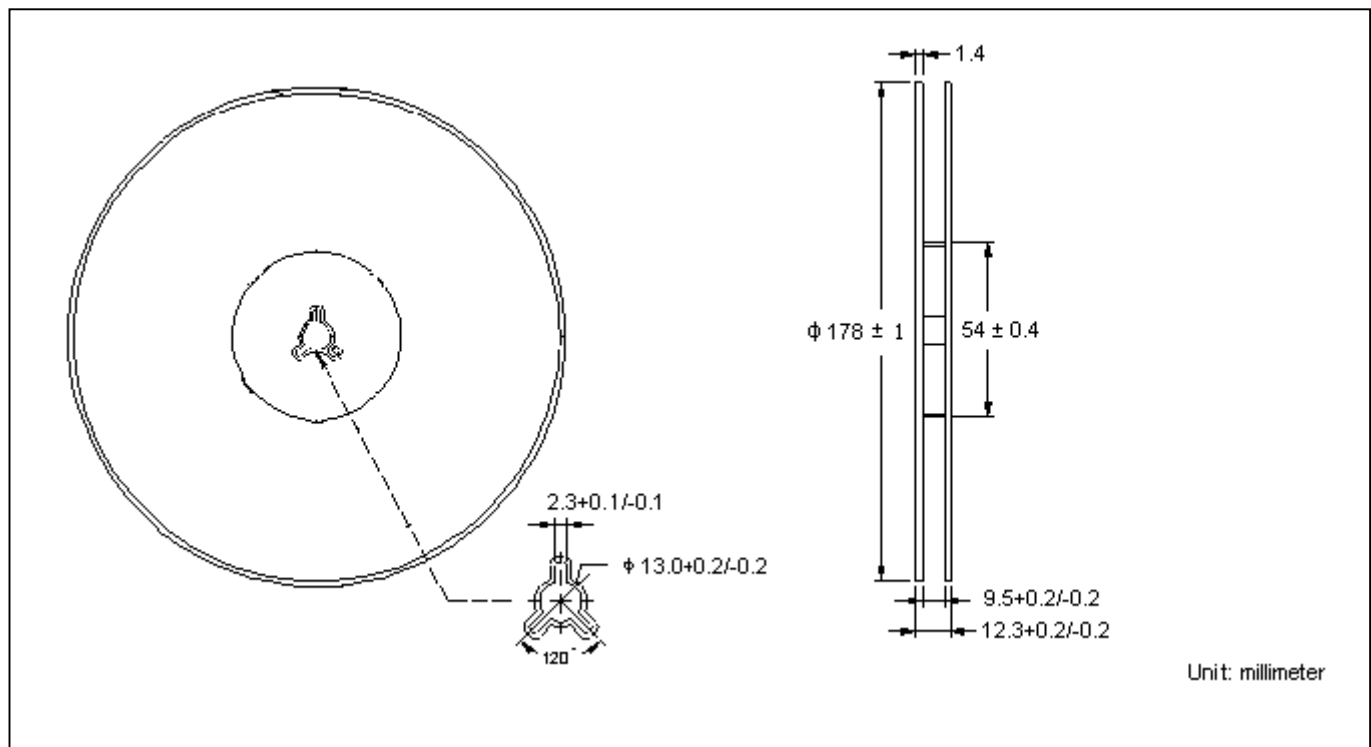
Single Pulse Power Rating, Junction to Ambient



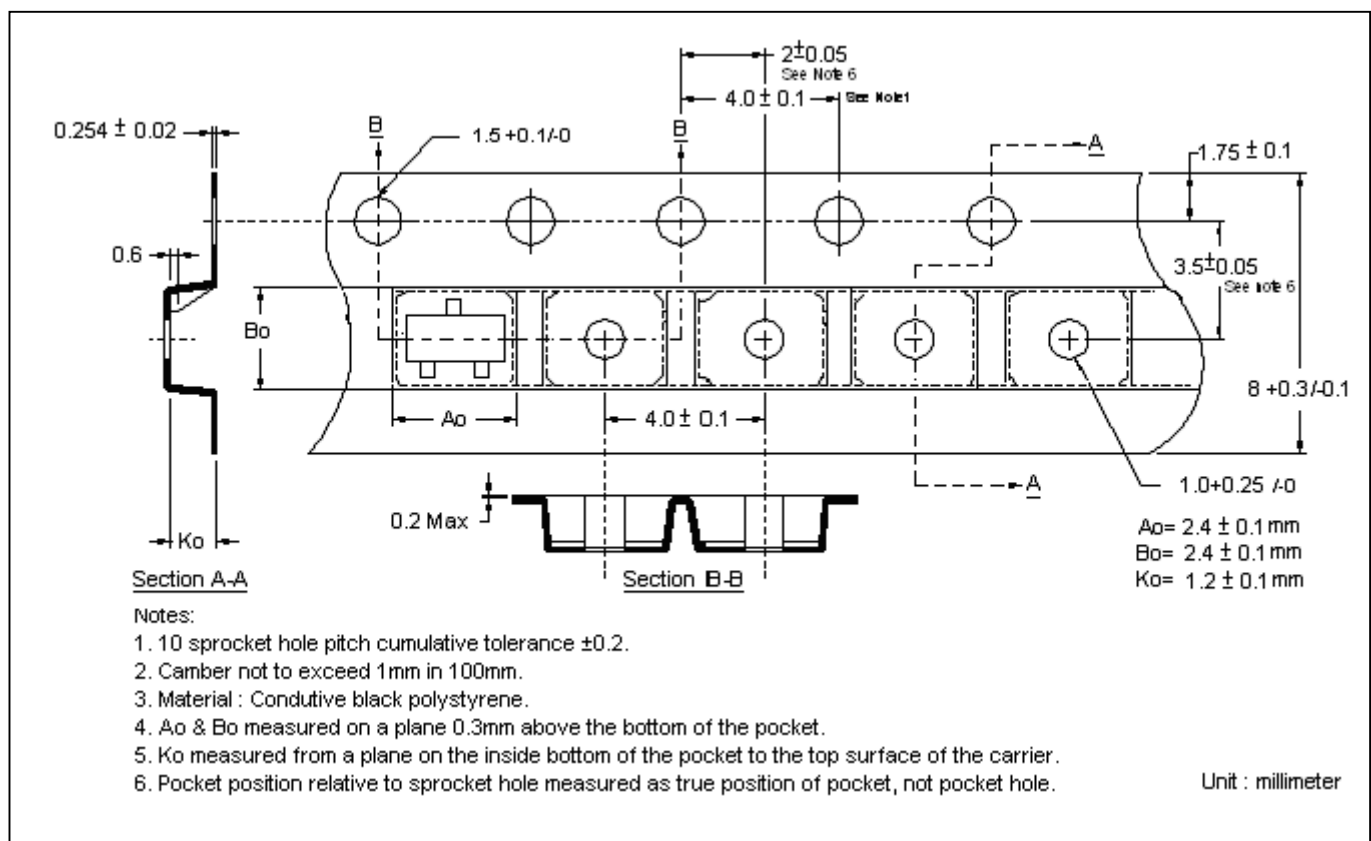
Transient Thermal Response Curves



Reel Dimension



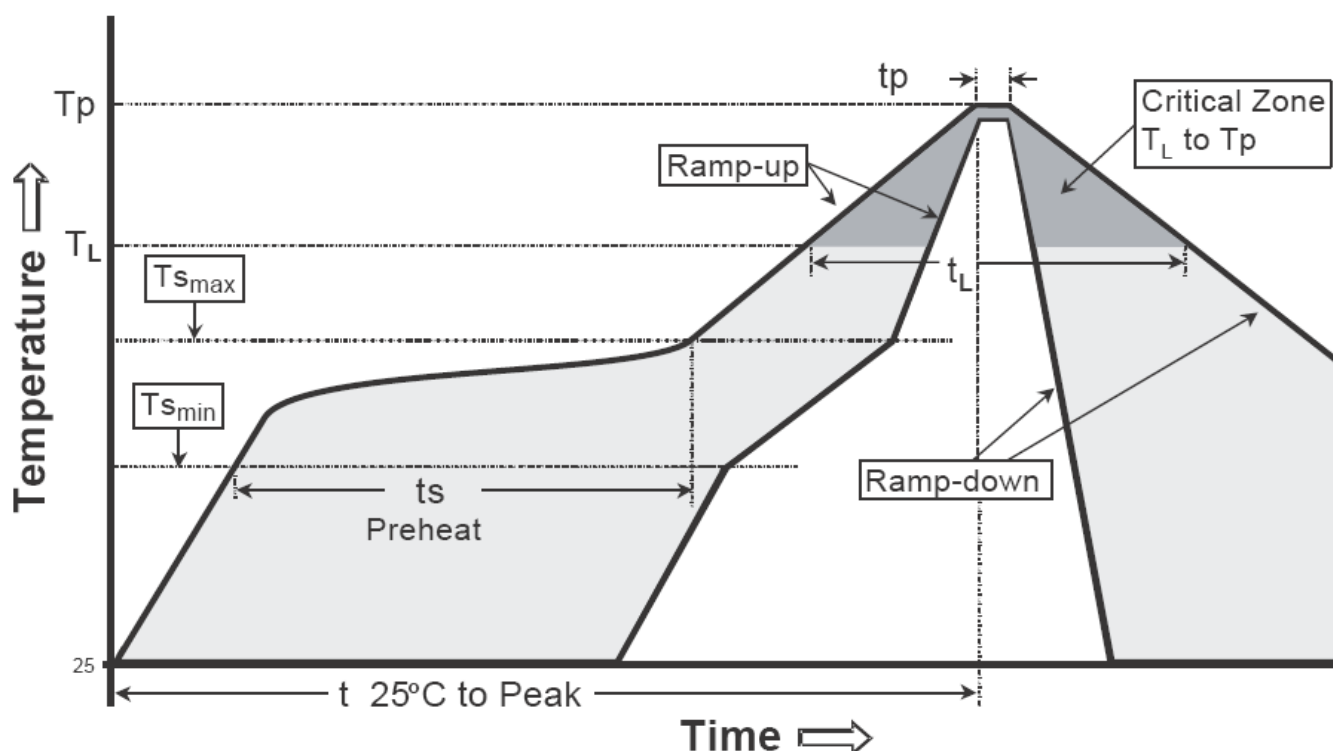
Carrier Tape Dimension



Recommended wave soldering condition

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

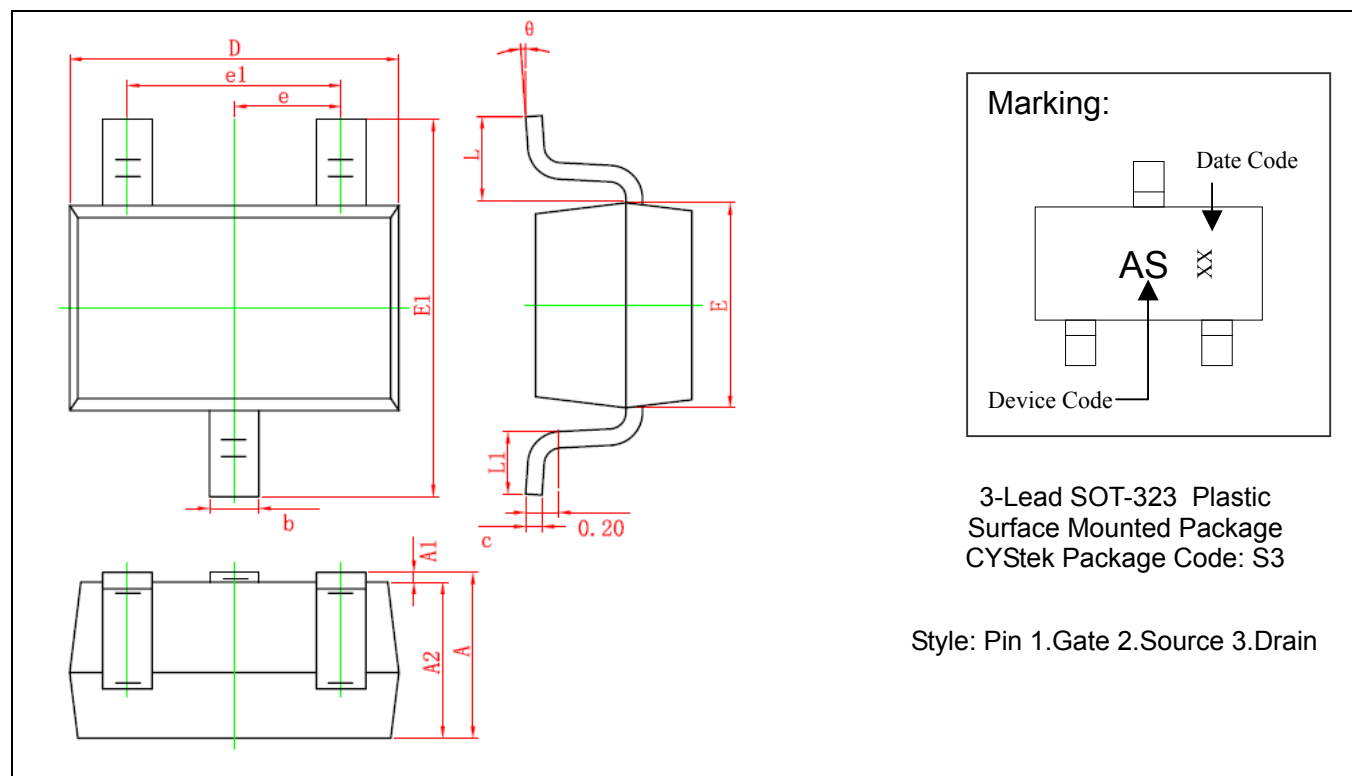
Recommended temperature profile for IR reflow



Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (Tsmax to Tp)	3°C/second max.	3°C/second max.
Preheat		
-Temperature Min(Ts min)	100°C	150°C
-Temperature Max(Ts max)	150°C	200°C
-Time(ts min to ts max)	60-120 seconds	60-180 seconds
Time maintained above:		
-Temperature (TL)	183°C	217°C
- Time (tL)	60-150 seconds	60-150 seconds
Peak Temperature(Tp)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

SOT-323 Dimension



DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.900	1.100	0.035	0.043	E1	2.150	2.450	0.085	0.096
A1	0.000	0.100	0.000	0.004	e	0.650	TYP	0.026	TYP
A2	0.900	1.000	0.035	0.039	e1	1.200	1.400	0.047	0.055
b	0.200	0.400	0.008	0.016	L	0.525	REF	0.021	REF
c	0.080	0.150	0.003	0.006	L1	0.260	0.460	0.010	0.018
D	2.000	2.200	0.079	0.087	θ	0°	8°	0°	8°
E	1.150	1.350	0.045	0.053					

Notes: 1.Controlling dimension: millimeters.

2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.

3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material:

- Lead: Pure tin plated.
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0.

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